

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		09/898,043	HAYASHI	
Examiner		Art Unit		Page 1 of 1
Johannes P Mondt		2826		

#### U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,172,382	01-2001	Nagahama et al.	257/94
*	B	US-6,377,597	04-2002	Okumura, Toshiyuki	372/45
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

#### FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	WO98/39827	09-1998	WIPO	Okumura, Toshiyuki	H01S 3/18
	O					
	P					
	Q					
	R					
	S					
	T					

#### NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	M. Levinshteyn et al, "Properties of Advanced Semiconductor Materials: GaN, AlN, InN, BN, SiC, SiGe", John Wiley & Sons (New York 2001; ISBN 0-471-35827-4), particularly pages 16, 39 and 58.
	V	S. Nakamura et al, "The Blue Laser Diode - The Complete Story", Springer Verlag (Berlin, Heidelberg, New York), Second Revised and Enlarged Edition (2000), ISBN: 3-540-66505-6; in particular pages 161-162.
	W	S. Nakamura, "Introduction to Nitride Semiconductor Blue Lasers and Light Emitting Diodes", Publ.: Taylor and Francis (New York, 2000, ISBN: 0-7484-0836-3), in particular: p. 357.
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.